

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CBR1-L010M SERIES
CBR2-L010M SERIES

SILICON BRIDGE RECTIFIER

CASE B-M

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR1-L010M, CBR2-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose applications.

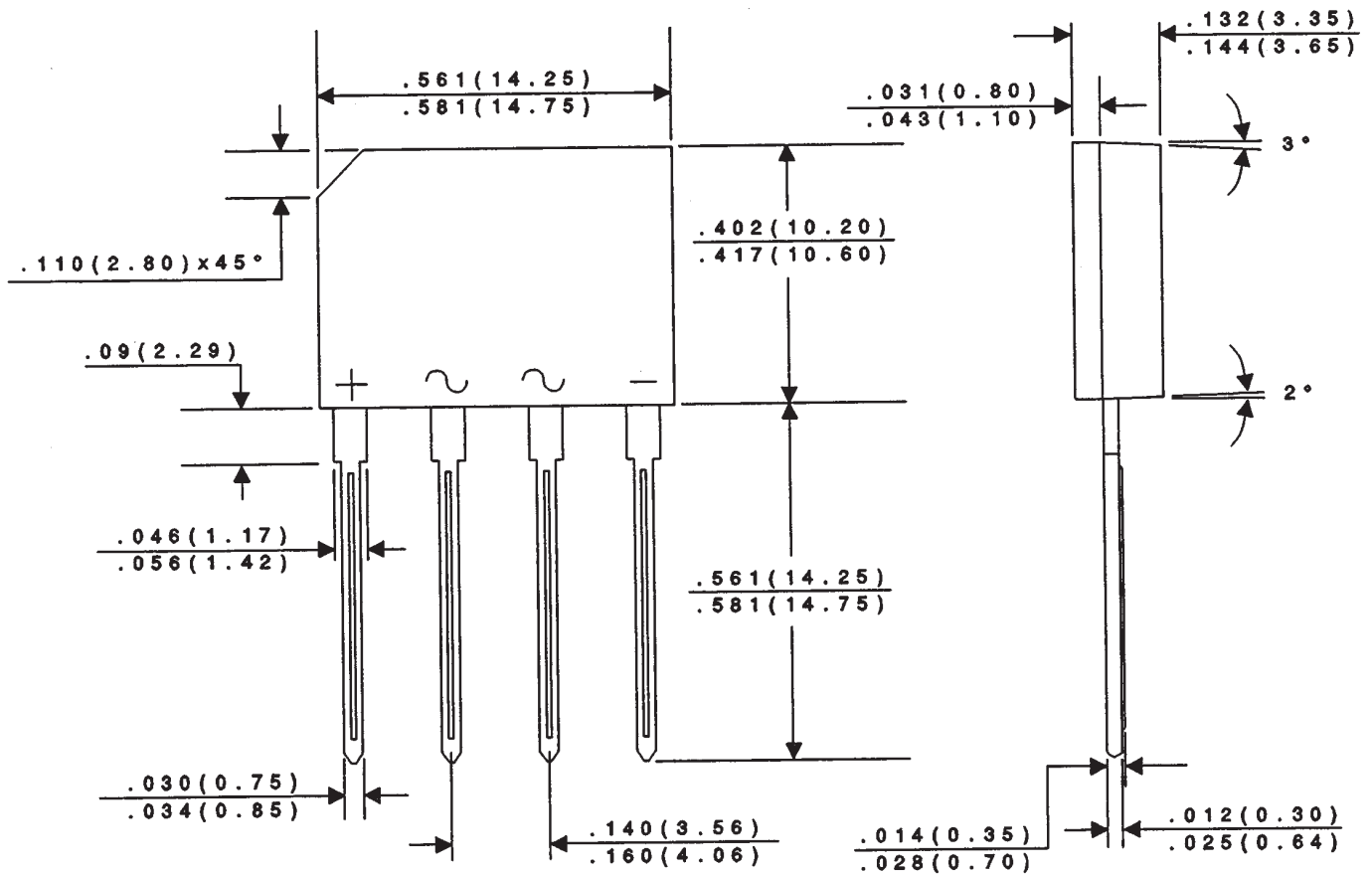
MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

		CBR1- L010M	CBR1- L020M	CBR1- L040M	CBR1- L060M	CBR1- L080M	CBR1- L100M	
		CBR2- L010M	CBR2- L020M	CBR2- L040M	CBR2- L060M	CBR2- L080M	CBR2- L100M	
	SYMBOL							UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_A = 50^\circ\text{C}$) (CBR1-L010M Series)	I_O				1.5			A
Average Forward Current ($T_A = 55^\circ\text{C}$) (CBR2-L010M Series)	I_O				2.0			A
Peak Forward Surge Current (CBR1-L010M Series)	I_{FSM}				50			A
Peak Forward Surge Current (CBR2-L010M Series)	I_{FSM}				60			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150				$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_F	$I_F = 1.0\text{A}$ (CBR1-L010M Series)		1.0	V
V_F	$I_F = 2.0\text{A}$ (CBR2-L010M Series)		1.1	V
I_R	$V_R = \text{Rated } V_{RRM}$		10	μA
I_R	$V_R = \text{Rated } V_{RRM}, T_A = 125^\circ\text{C}$		500	μA

CASE B-M - MECHANICAL OUTLINE



All Dimensions in Inches (mm).